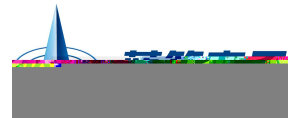


/ Revised record

D	2018-7				
E	2018-10-16				
F	2019-3-13	2		.	
G	2020-1-8	2 3 6	$V_{GS(th)}$! " # \$ % & ' \$ () * + # \$, - & ' \$ () . V_{GSS} ! " ± 20 改 为 $\pm 12V$; I_{GSS} 的条件 ! " $V_{GS} = \pm 20V$ 改为 $V_{GS} = \pm 12V$;		



SOP-8

MOS

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

N-channel

P-channel

 $V_{DS}(V)=30V$ $V_{DS}(V)=-30V$ $I_D=6.9A$ $I_D=-6A$ $R_{DS(ON)} < 32m\ \Omega$ ($V_{GS}=10V$) $R_{DS(ON)} < 65m\ \Omega$ ($V_{GS}=-10V$) $R_{DS(ON)} < 36m\ \Omega$ ($V_{GS}=4.5V$) $R_{DS(ON)} < 75m\ \Omega$ ($V_{GS}=-4.5V$)

Halogen-free Product.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies. And suitable for use as a load switch or in PWM applications.



参数 Parameter	符号 Symbol	数值 Rating		单位 Unit
		N-channel	P-channel	
Drain-Source Voltage	V_{DSS}			V
Gate-Source Voltage	V_{GSS}	± 12		V
Continuous Drain Current I_D ($T_A = 25^\circ\text{C}$)	$I_D (T_A = 25^\circ\text{C})$	6.9	-	
	$I_D (T_A)$	5.8	-	
Pulsed Drain Current I_{DM}	I_{DM}			

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	30	30		

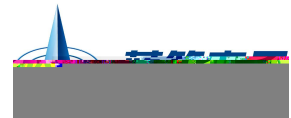
N- / N-



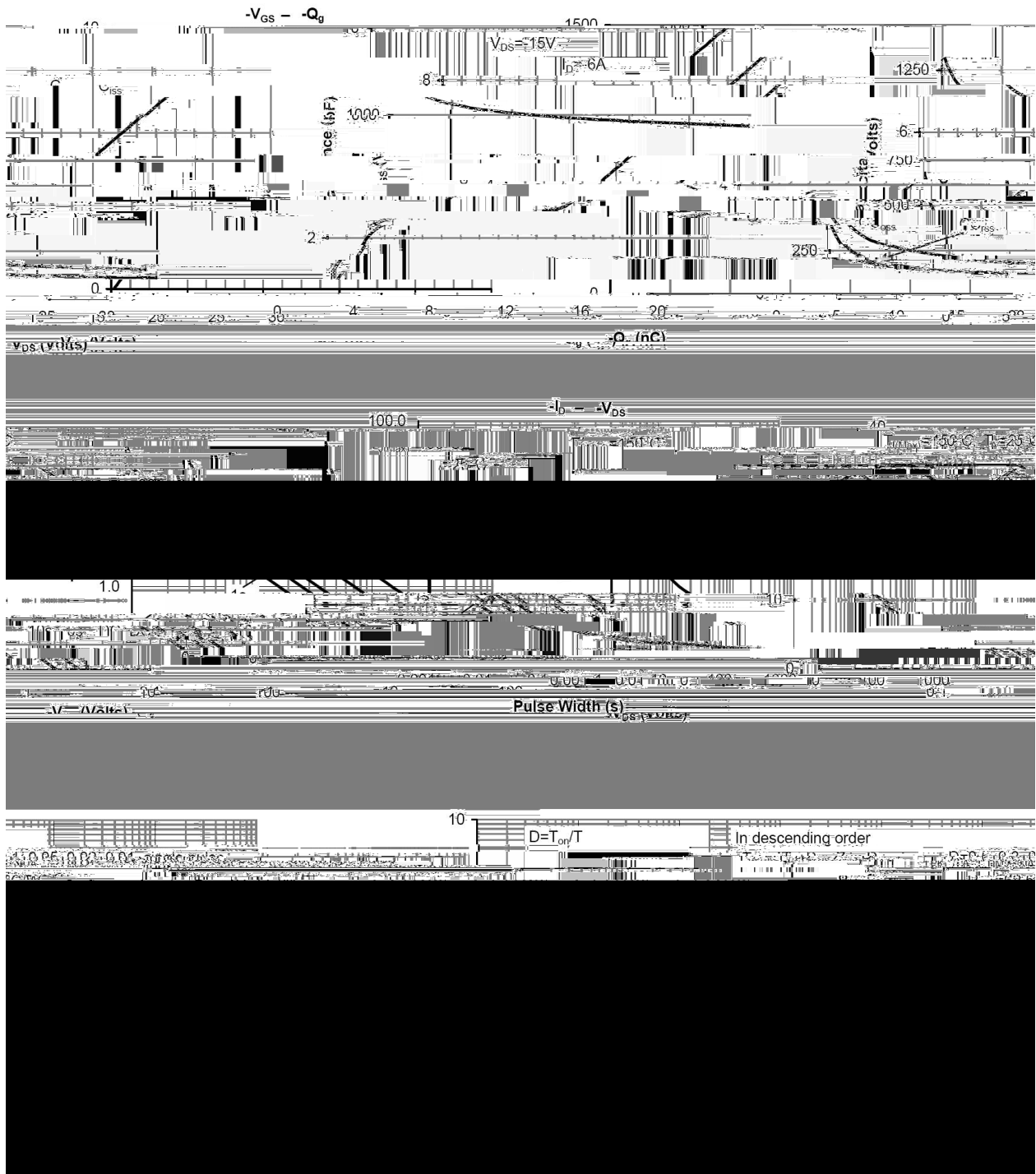
Parameter		Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}				

P- / P-CHANNEL Electrical Characteristic Curve





P- / P-CHANNEL Electrical Characteristic Curve

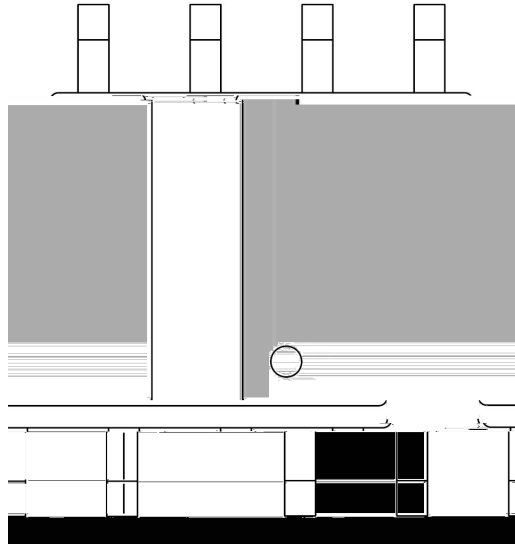




/ Package Dimensions



/ Marking Instructions



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



					Note:
1	150	180	60	90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5		K		